

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	18mΩ @ V _{GS} = 10V	43A
	20mΩ @ V _{GS} = 4.5V	41A

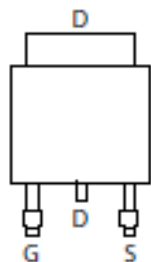
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

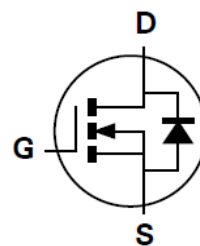
- Power Management Functions
- DC-DC Converters
- Industrial



Top View



Pin Out Top View



Equivalent Circuit

Features

- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

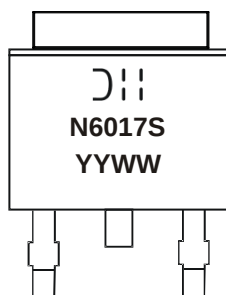
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6017SK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



D = Manufacturer's Marking
 N6017S = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 17 = 2017)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	T _C = +25°C	I _D	43	A
	T _C = +70°C		34	
	T _A = +25°C	I _D	11	A
	T _A = +70°C		8.8	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)		I _{DM}	70	A
Maximum Continuous Body Diode Forward Current (Note 5)		I _S	3.6	A
Avalanche Current, L = 0.1mH		I _{AS}	25	A
Avalanche Energy, L = 0.1mH		E _{AS}	32	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	3.3	W
	T _C = +25°C		50	
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	38	°C/W
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	2.5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	µA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	18	mΩ	V _{GS} = 10V, I _D = 6A
		-	-	20		V _{GS} = 4.5V, I _D = 4A
Diode Forward Voltage	V _{SD}	-	-	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	2711	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	-	152	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	126	-	pF	
Gate Resistance	R _g	-	1.4	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	26	-	nC	V _{DS} = 48V, I _D = 6A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	55	-	nC	
Gate-Source Charge	Q _{gs}	-	6.2	-	nC	
Gate-Drain Charge	Q _{gd}	-	8.5	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	4.9	-	ns	V _{DD} = 30V, V _{GS} = 10V, R _g = 3.3Ω, I _D = 6A
Turn-On Rise Time	t _r	-	5.4	-	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	38.2	-	ns	
Turn-Off Fall Time	t _f	-	11	-	ns	
Reverse Recovery Time	t _{RR}	-	16.6	-	ns	I _F = 6A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	-	10.3	-	nC	

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to product testing.

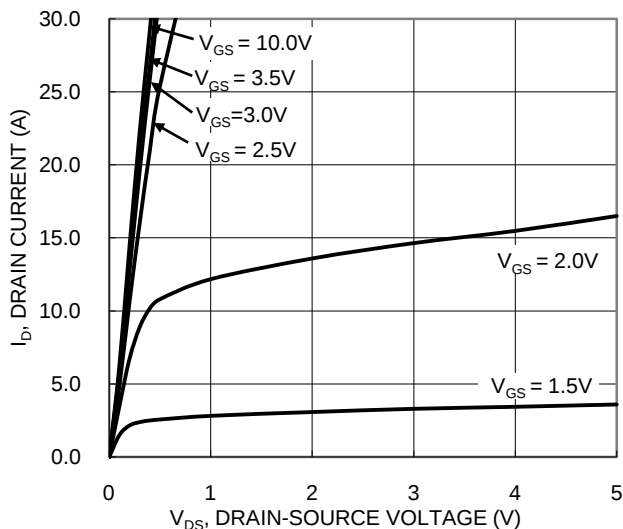


Figure 1. Typical Output Characteristic

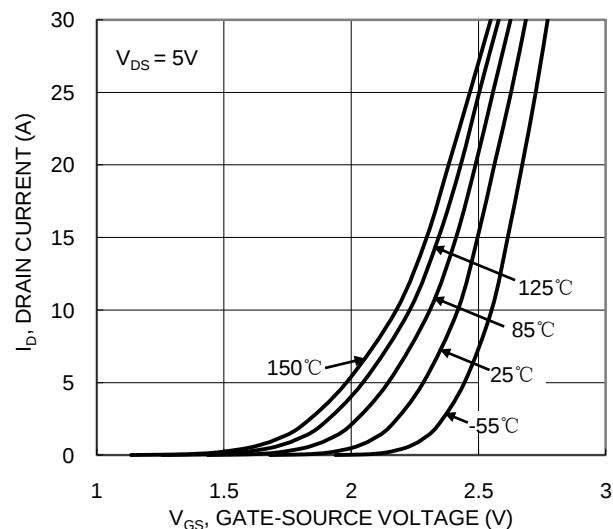


Figure 2. Typical Transfer Characteristic

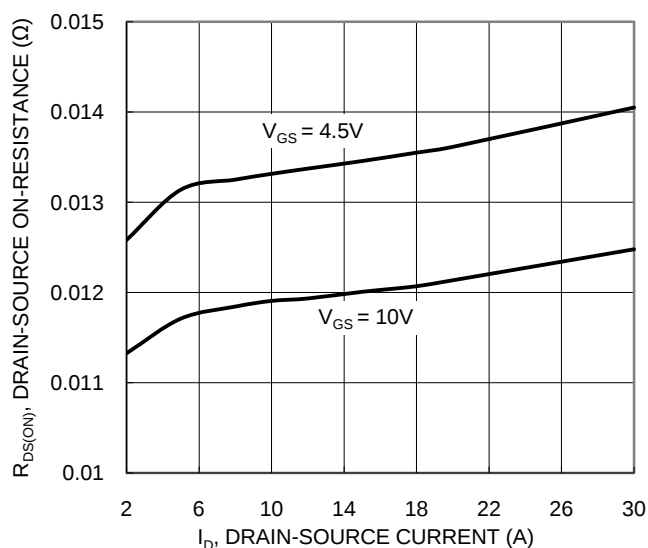


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

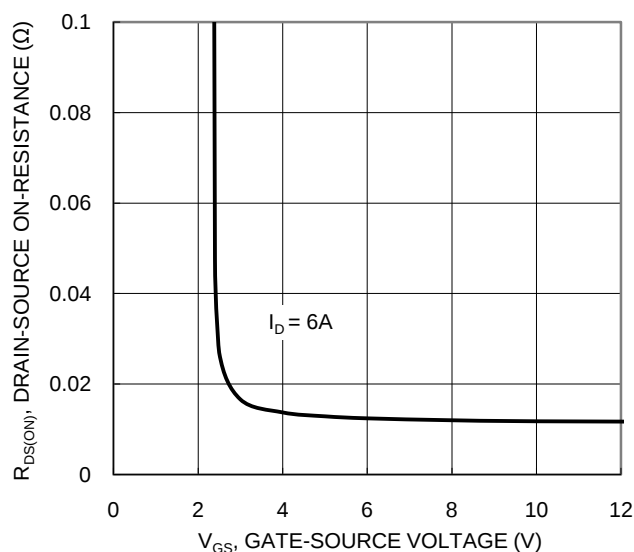


Figure 4. Typical Transfer Characteristic

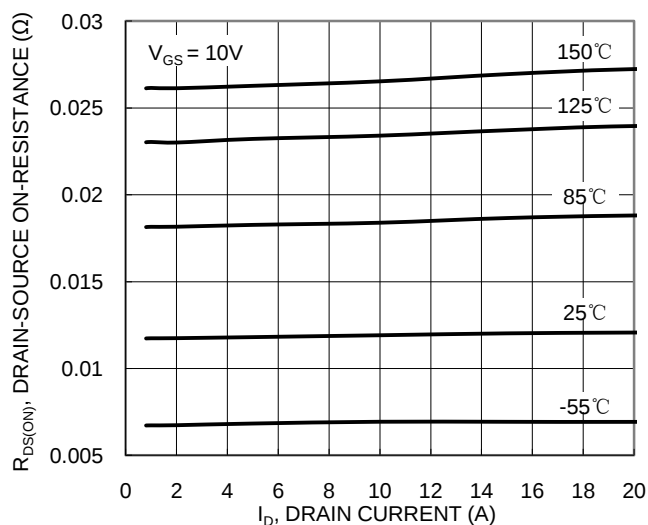


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

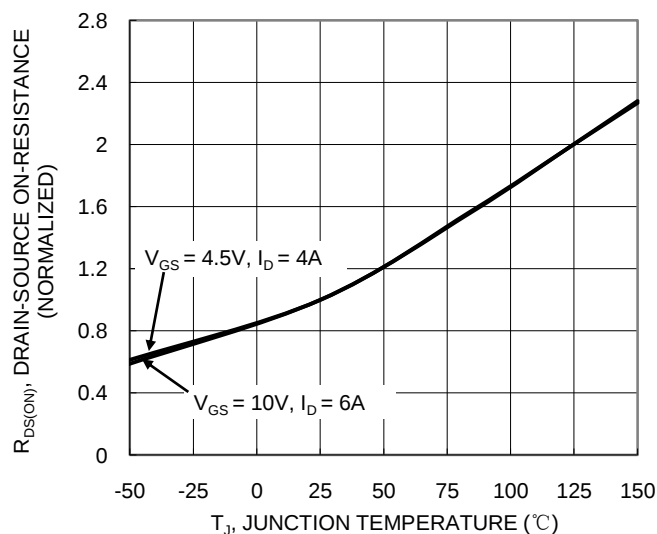


Figure 6. On-Resistance Variation with Temperature

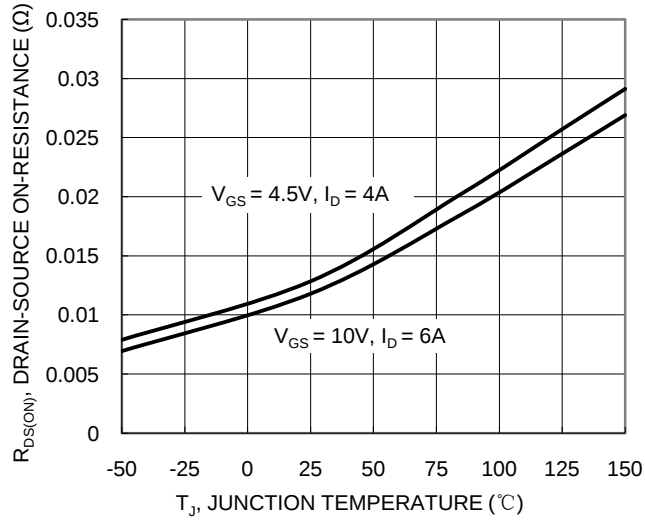


Figure 7. On-Resistance Variation with Temperature

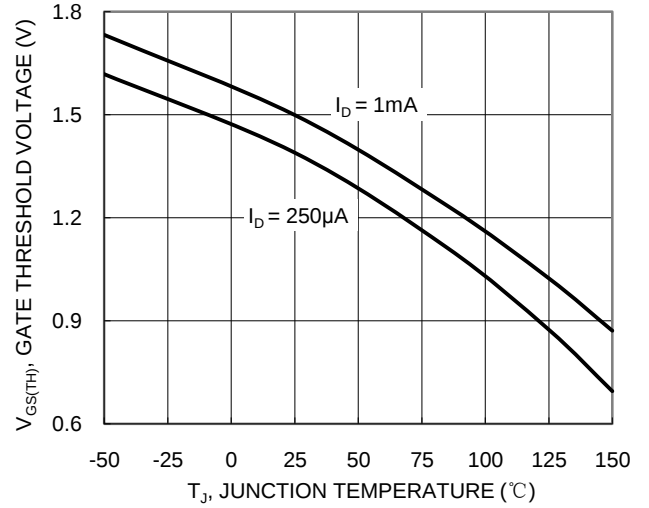


Figure 8. Gate Threshold Variation vs. Temperature

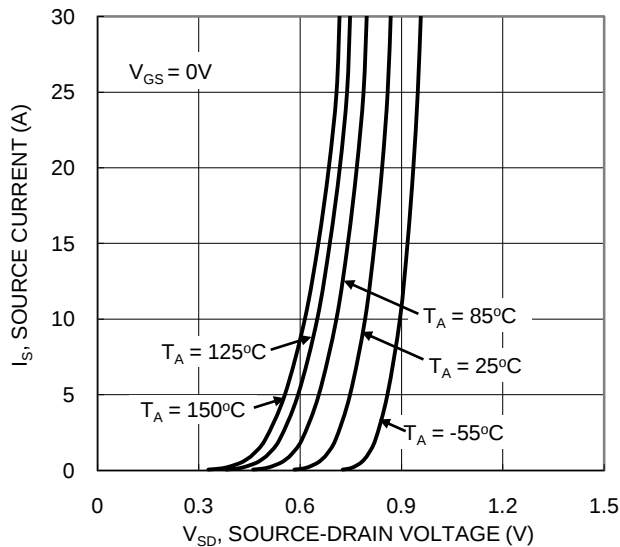


Figure 9. Diode Forward Voltage vs. Current

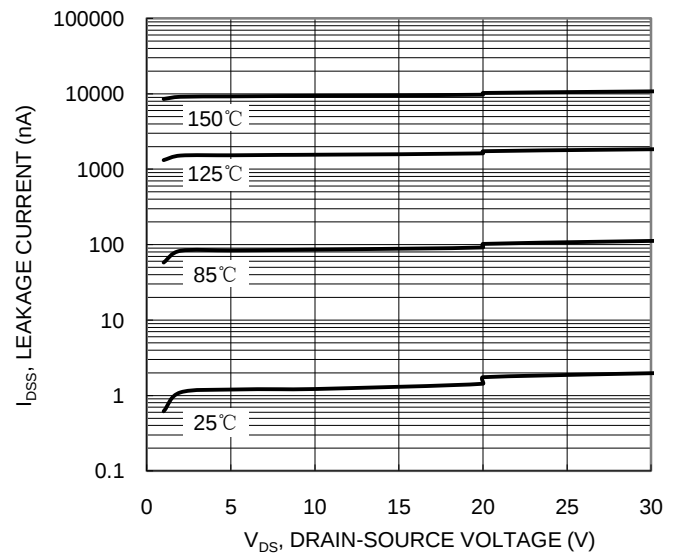


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

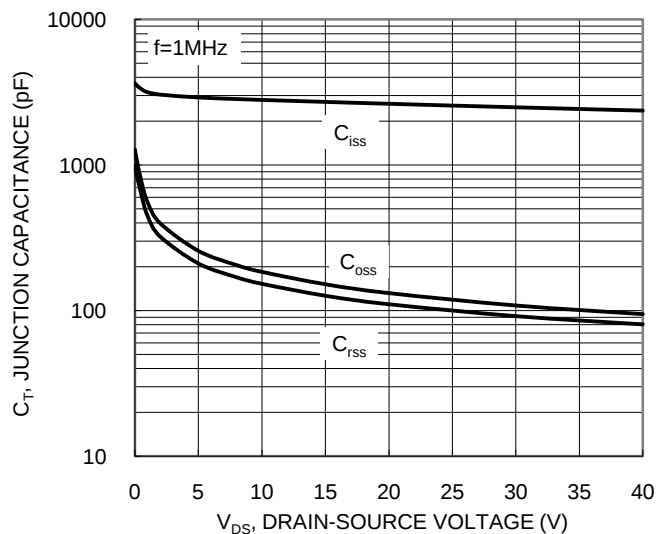


Figure 11. Typical Junction Capacitance

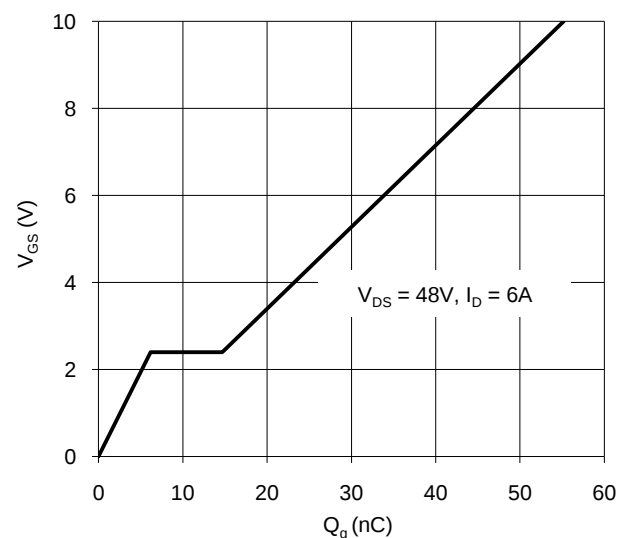
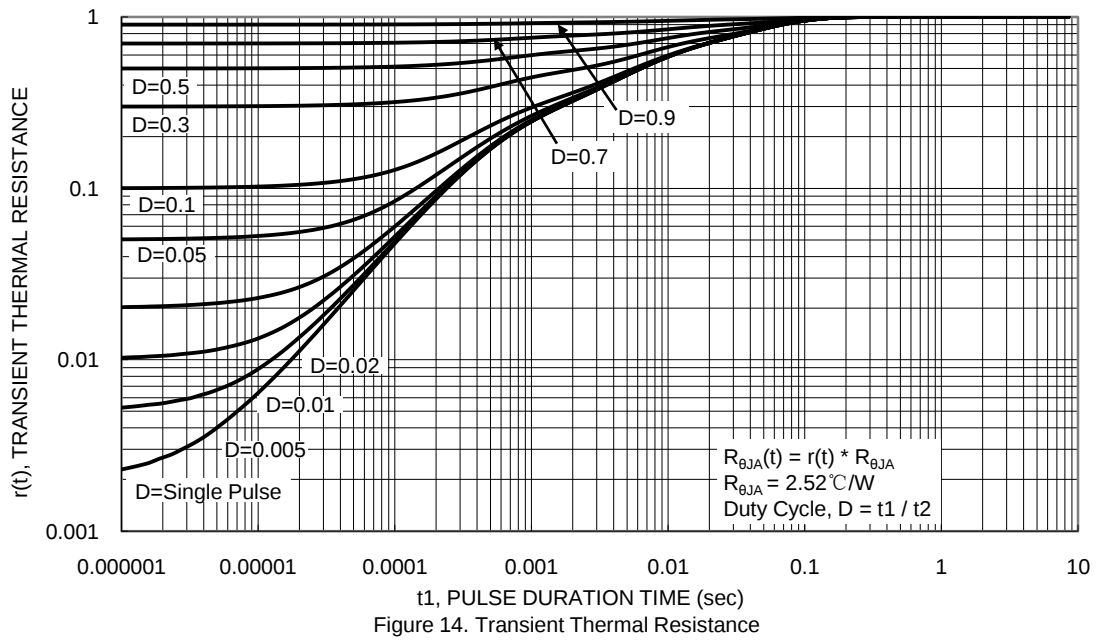
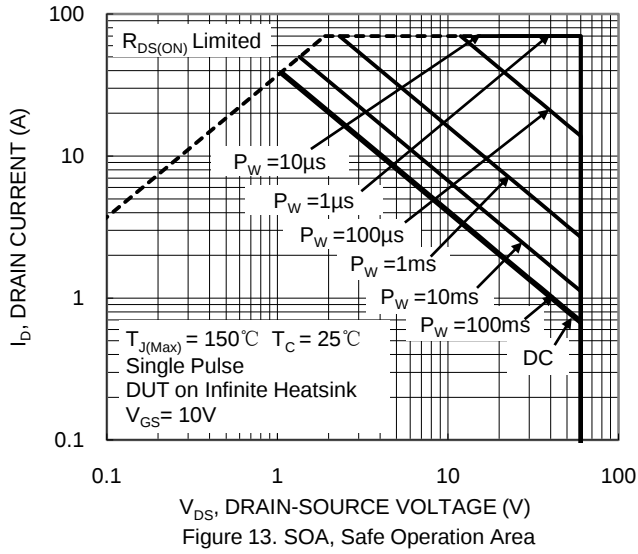


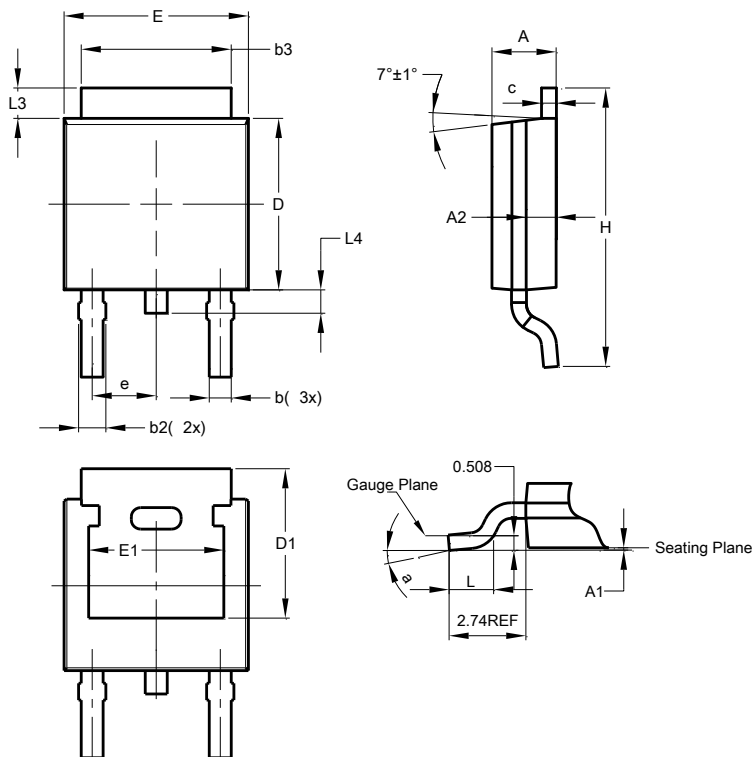
Figure 12. Gate Charge



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

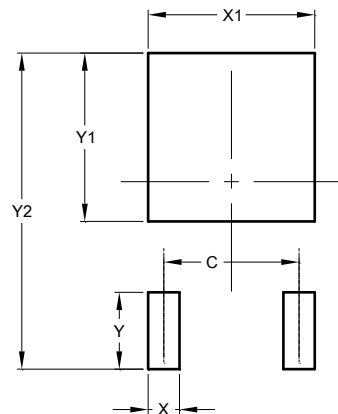


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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